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Inclosure Material:

Metal all transistor

Overall Length:

0.170 inches all transistor and 0.210 inches all transistor

Terminal Length:

0.500 inches all transistor

Overall Diameter:

0.209 inches all transistor and 0.230 inches all transistor

Internal Configuration:

Field effect all transistor

Channel Polarity And Control Type (non-core):

P-channel junction type all transistor

Electrode Internally-electrically Connected To Case:

Gate all transistor

Component Function Relationship:

Matched

Component Name And Quantity:

2 transistor

Mounting Method:

Terminal all transistor

Terminal Circle Diameter:

0.100 inches all transistor

Semiconductor Material:

Silicon all transistor

Voltage Rating In Volts Per Characteristic:

30.0 gate to source voltage all transistor

Current Rating Per Characteristic:

10.00 nanoamperes zero-gate-voltage source current watts all transistor

Power Rating Per Characteristic:

300.0 milliwatts small-signal input power, common-collector absolute all transistor

Maximum Operating Temperature Per Measurement Point:

100.0 degrees celsius ambient air all transistor

Terminal Type And Quantity:

3 pin all transistor

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fig:

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